Raduga 396 Full Release

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party. November 26, 2009 Gonzalez Performing Group will feature a talent contest and an eight-hour dance party at the celebration. November 24, 2009 Bermuda's Liz Gomarus is bringing her "Save the Men" entertainment marathon to DTMC. October 24, 2009 Ashley Young launches her new solo album, "Why Do We Live Here," with a concert at the Bermuda Arts Centre. September 25, 2009 The 50th anniversary celebration of the Bermuda Sailors Benevolent Society is held at the Royal Naval Dockyard in St. George's.A flash memory is generally classified as either an EEPROM or a mask ROM. The former memory is programmed (i.e., erased and reprogrammed) by a user, and the latter is permanently programmed during manufacture. A typical EEPROM memory cell is programmed by storing charges in a floating gate to create a threshold voltage V.sub.t above and below the drain voltage (V.sub.d) under control of a control gate voltage (V.sub.g). The cell is programmed

by applying a control gate voltage V.sub.g of about 5 volts and a drain voltage V.sub.d of about -5 volts to the selected memory cell. The drain voltage V.sub.d and control gate voltage V.sub.g are provided by wordlines and a select gate voltage V.sub.s. A select gate voltage V.sub.s will turn on the cell and a wordline voltage V.sub.w is applied to the selected wordline, such as the wordline at the select gate for the memory cell. The source is usually grounded. The memory cell can be read by applying a control gate voltage V.sub.g of about 5 volts and a drain voltage V.sub.d of about 3 volts to the selected memory cell, so that the voltage on the control gate of the selected cell is insufficient to cause current flow through the channel under conditions where the drain voltage V.sub.d is above the threshold voltage V.sub.t. The wordline voltage V.sub.w is typically on. The current flowing through the cell from drain to source depends on the state of the cell. The current is lower when the threshold voltage is below about 0.8 volts, which occurs when the cell is in a programmed state. The current is higher when the threshold voltage is above about 4 volts, which occurs when 82157476af